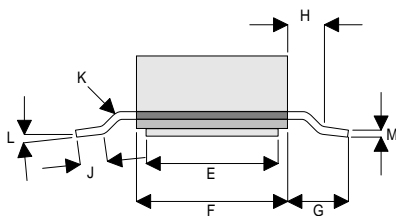
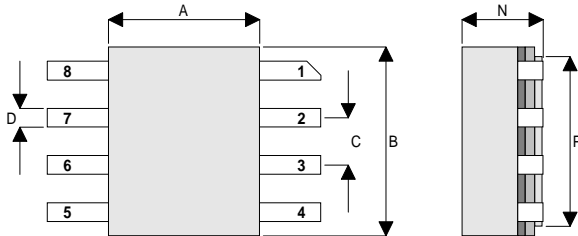


MECHANICAL DATA

**GOLD METALLISED
MULTI-PURPOSE SILICON
DMOS RF FET
5W – 12.5V – 1GHz
PUSH-PULL**



SO8 PACKAGE

- PIN 1 – SOURCE
- PIN 2 – DRAIN 1
- PIN 3 – DRAIN 2
- PIN 4 – SOURCE
- PIN 5 – SOURCE
- PIN 6 – GATE 2
- PIN 7 – GATE 1
- PIN 8 – SOURCE

FEATURES

- SIMPLIFIED AMPLIFIER DESIGN
- SUITABLE FOR BROAD BAND APPLICATIONS
- VERY LOW C_{rss}
- SIMPLE BIAS CIRCUITS
- LOW NOISE
- HIGH GAIN – 10 dB MINIMUM

APPLICATIONS

- HF/VHF/UHF COMMUNICATIONS
from 1MHz to 1GHz

Dim.	mm	Tol.	Inches	Tol.
A	4.06	±0.08	0.160	±0.003
B	5.08	±0.08	0.200	±0.003
C	1.27	±0.08	0.050	±0.003
D	0.51	±0.08	0.020	±0.003
E	3.56	±0.08	0.140	±0.003
F	4.06	±0.08	0.160	±0.003
G	1.65	±0.08	0.065	±0.003
H	0.76	+0.25 -0.00	0.030	+0.010 -0.000
J	0.51	Min.	0.020	Min.
	1.02	Max.	0.040	Max.
K	45°	Max.	45°	Max.
L	0°	Min.	0°	Min.
	7°	Max.	7°	Max.
M	0.20	±0.08	0.008	±0.003
N	2.18	Max.	0.086	Max.
P	4.57	±0.08	0.180	±0.003

ABSOLUTE MAXIMUM RATINGS ($T_{case} = 25^{\circ}C$ unless otherwise stated)

P_D	Power Dissipation	17.5W
BV_{DSS}	Drain – Source Breakdown Voltage	40V
BV_{GSS}	Gate – Source Breakdown Voltage	±20V
$I_{D(sat)}$	Drain Current	4A
T_{stg}	Storage Temperature	-65 to 150°C
T_j	Maximum Operating Junction Temperature	200°C

ELECTRICAL CHARACTERISTICS ($T_{case} = 25^{\circ}C$ unless otherwise stated)

Parameter		Test Conditions		Min.	Typ.	Max.	Unit
PER SIDE							
BV_{DSS}	Drain–Source Breakdown Voltage	$V_{GS} = 0$	$I_D = 10mA$	40			V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 12.5V$	$V_{GS} = 0$			1	mA
I_{GSS}	Gate Leakage Current	$V_{GS} = 20V$	$V_{DS} = 0$			1	μA
$V_{GS(th)}$	Gate Threshold Voltage*	$I_D = 10mA$	$V_{DS} = V_{GS}$	0.5		7	V
g_{fs}	Forward Transconductance*	$V_{DS} = 10V$	$I_D = 0.2A$	0.18			S
TOTAL DEVICE							
G_{PS}	Common Source Power Gain	$P_O = 5W$		10			dB
η	Drain Efficiency	$V_{DS} = 12.5V$	$I_{DQ} = 0.2A$	40			%
VSWR	Load Mismatch Tolerance	$f = 1GHz$		20:1			—
PER SIDE							
C_{iss}	Input Capacitance	$V_{DS} = 0V$	$V_{GS} = -5V$ $f = 1MHz$			12	pF
C_{oss}	Output Capacitance	$V_{DS} = 12.5V$	$V_{GS} = 0$ $f = 1MHz$			10	pF
C_{rss}	Reverse Transfer Capacitance	$V_{DS} = 12.5V$	$V_{GS} = 0$ $f = 1MHz$			1	pF

* Pulse Test: Pulse Duration = 300 μs , Duty Cycle $\leq 2\%$

THERMAL DATA

$R_{THj-case}$	Thermal Resistance Junction – Case	Max. 6°C / W
----------------	------------------------------------	--------------